

**SILICON NPN TRIPLE DIFFUSED TYPE****2SC3182**

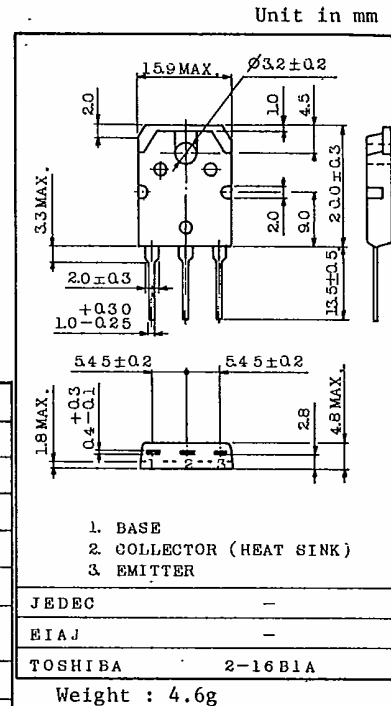
POWER AMPLIFIER APPLICATIONS.

## FEATURES:

- Complementary to 2SA1265
- Recommend for 70W High Fidelity Audio Frequency Amplifier Output Stage

## MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V <sub>CB0</sub>	140	V
Collector-Emitter Voltage	V <sub>CE0</sub>	140	V
Emitter-Base Voltage	V <sub>EB0</sub>	5	V
Collector Current	I <sub>C</sub>	10	A
Base Current	I <sub>B</sub>	1	A
Collector Power Dissipation (Tc=25°C)	P <sub>C</sub>	100	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	-55 ~ 150	°C



## ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I <sub>CB0</sub>	V <sub>CB</sub> =140V, I <sub>E</sub> =0	-	-	5.0	μA
Emitter Cut-off Current	I <sub>EB0</sub>	V <sub>EB</sub> =5V, I <sub>C</sub> =0	-	-	5.0	μA
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =50mA, I <sub>B</sub> =0	140	-	-	V
DC Current Gain	h <sub>FE(1)</sub> (Note)	V <sub>CE</sub> =5V, I <sub>C</sub> =1A	55	-	160	
	h <sub>FE(2)</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =5A	35	83	-	
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =7A, I <sub>B</sub> =0.7A	-	0.3	2.0	V
Base-Emitter Voltage	V <sub>BE</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =5A	-	0.9	1.5	V
Transition Frequency	f <sub>T</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =1A	-	30	-	MHz
Collector Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz	-	220	-	pF

Note : h<sub>FE(1)</sub> Classification R : 55~110, O : 80~160

TOSHIBA CORPORATION

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